

# Supporting Information

## Enhanced Electrochemical Performance by Facile Oxygen Vacancies from Lower Valence-State Doping for Ramsdellite- $\text{MnO}_2$

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Table S1 Formation energies of substitutional doping on the surfaces for R- $\text{MnO}_2$ . (Units: eV)

	<b>110</b>			<b>010</b>		
<b>Doping sites</b>	<b>SS</b>	<b>SF</b>	<b>NS</b>	<b>SS</b>	<b>SF</b>	<b>NS</b>
<b>Zn-doped</b>	6.70	5.27	6.70	6.29	5.52	6.80

Table S2 Formation energies for the dilute oxygen vacancy at surfaces of NS Zn-doped R-MnO<sub>2</sub>.

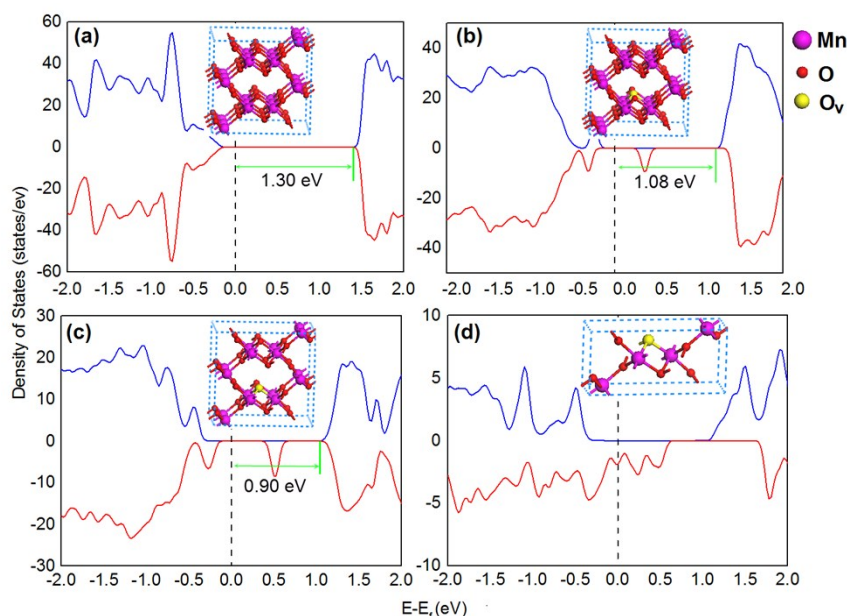
(Units: eV)

	<b>Vacancy</b>	<b>Zn-doping</b>
	<b>Sites</b>	<b>NS</b>
<b>110</b>	<b>I</b>	0.08
	<b>II</b>	1.48
<b>010</b>	<b>I</b>	0.58
	<b>II</b>	1.39

Table S3 Predicted magnetic moments of surface Mn/Zn atoms on low energy surfaces for pristine and Zn-doped R-MnO<sub>2</sub>.

<b>Doping sites</b>	<b>Mn/Zn sites</b>	<b>Pristine</b>	<b>Zn-doping</b>		<b>Zn-doping with vacancy I</b>	
			<b>SS</b>	<b>SF</b>	<b>SS</b>	<b>SF</b>
<b>bulk</b>		3.02				
<b>110</b>	<b>SS</b>	3.13	- 0.08	3.13	- 0.03	3.19
	<b>SF</b>	3.36	3.78	0.00	3.85	0.03
<b>010</b>	<b>SS</b>	3.15	- 0.03	3.14	- 0.14	3.26
	<b>SF</b>	3.38	3.25	- 0.01	3.28	-0.16

Figure S1 The total density of states for  $1\times 2\times 3$  supercell without vacancy,  $1\times 2\times 3$ ,  $1\times 2\times 2$  and  $1\times 1\times 1$  supercell with one vacancy of R-MnO<sub>2</sub>.



As shown in Figure S1, four models are chosen as  $1\times 2\times 3$  supercell without vacancy,  $1\times 2\times 3$ ,  $1\times 2\times 2$  and  $1\times 1\times 1$  supercell with one vacancy, to represent four oxygen concentrations 0.00%, 2.08%, 3.12% and 12.50%, respectively. The total density of states for these modes are also shown in Figure S1. After introducing oxygen oxides, it could be seen that the conduction-band minimum will shift down gradually because of the broken of Mn-O bonds, and some impurity peaks are introduced within the band gap. It could be calculated out that the band gaps of these structures are 1.30 eV, 1.08 eV, 0.90 eV and 0.00 eV, respectively. In other words, the band gap will be narrowed down gradually with the increasing of oxygen vacancies concentration and the MnO<sub>2</sub> will be metallic finally. Therefore, the band gap reduction of bulk MnO<sub>2</sub> after introducing oxygen vacancy is crucial to enhancing the electric conductivity.

Figure S2 Partial density of states of NS Zn-doped R-MnO<sub>2</sub>.

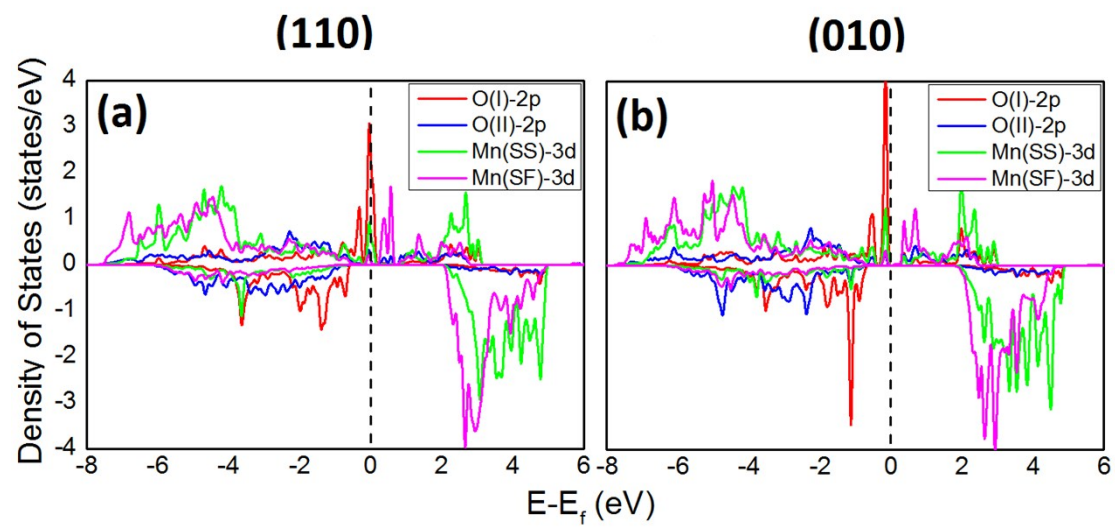


Figure S3 Charge density difference of NS Zn-doped R-MnO<sub>2</sub>.

